OPB0505P

Silicon Photo Transistor



1. Structure

1.1 Chip Size : 0.50mm X 0.50mm
1.2 Chip thickness : 180±20um
1.3 Metallization : Top - Al, Bottom - Cr-Au
1.4 Passivation : Silicon Nitride
1.5 Bonding Pad Size
- Emitter : 120 X 120um
- Base : 60um X 60um

2. Electrical Characteristics

(Ta=25℃)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
C-E Breakdown Voltage	BV_{CEO}	30			V	I_{CE}=100uA
C-B Breakdown Voltage	BV_{CBO}	30			V	I_{CE}=10uA
E-B Breakdown Voltage	BV_{EBO}	5			V	I_{CB}=10uA
E-C Breakdown Voltage	BV_{ECO}	5			V	I_{EC}=10uA
Collector Cut-Off Current	I_{CEO}			100	nA	V_{CE}=20V
C-E Saturation Voltage	V_{CES}			300	mV	I_C=2mA, I_B=100uA
DC Current Gain	h_{FE}	200			-	V_{CE}=5V, Ic=2mA

3. Maximum Ratings

(Ta=25℃)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	Ic	100	mA
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to+150	℃

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